

7/5/4
7/19/07

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

Inventor(s): ITO et al.

Filed: Herewith

Title: GROUP III NITRIDE COMPOUND SEMICONDUCTOR DEVICE

December 18, 2001

PRELIMINARY AMENDMENT

Hon. Commissioner of Patents
Washington, D.C. 20231

Sir:

Please amend this application as follows:

IN THE SPECIFICATION:

At the top of the first page, just under the title, insert:

A1
This is a Divisional of U.S. Application No. 09/518,724, filed March 3, 2000,
the entire contents of which are incorporated by reference.

Please amend the specification as follows:

Page 1, delete the whole paragraph starting with line 5 and replace it with the
following new paragraph.

Aγ
This invention relates to a group III nitride compound semiconductor device. More
particularly, it relates to an improvement in an undercoat layer for a group III nitride
compound semiconductor layer such as a GaN semiconductor layer.